

isc Silicon PNP Power Transistors

2SB551

**DESCRIPTION**

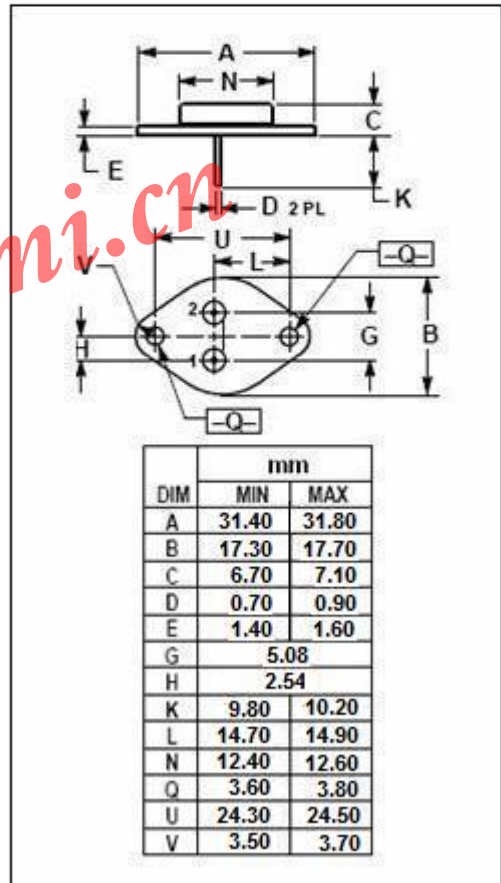
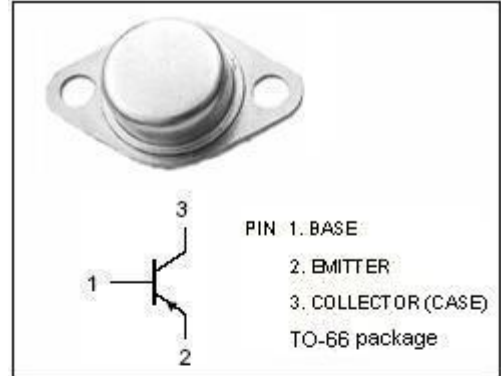
- Low Collector Saturation Voltage-  
:  $V_{CE(sat)} = -1.2V(Typ.) @ I_C = -2A$
- High Power Dissipation-  
:  $P_C = 25W(Max) @ T_C = 55^\circ C$

**APPLICATIONS**

- Designed for low frequency power amplifier applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-50	V
$V_{CEO}$	Collector-Emitter Voltage	-50	V
$V_{EBO}$	Emitter-Base Voltage	-4	V
$I_C$	Collector Current-Continuous	-3	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ C$	25	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature	-45~150	$^\circ C$



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## ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -50mA; R <sub>BE</sub> = ∞	-50			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -5mA; I <sub>E</sub> = 0	-50			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -5mA; I <sub>C</sub> = 0	-4			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -2A; I <sub>B</sub> = -0.2A			1.2	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -1A; V <sub>CE</sub> = -4V			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -20V; I <sub>E</sub> = 0			-0.1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -4V	35		200	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -0.1A; V <sub>CE</sub> = -4V	35			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -4V	15			MHz

◆ h<sub>FE-1</sub> Classifications

A	B	C
35-70	60-120	100-200